

We focus on power.

20.09.2012

RIDGE WAVEGUIDE LASER

GaAs Semiconductor Laser Diode Fabry-Perot Laser







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General Product Information

Product	Application	
930 nm Fabry-Perot Laser with hermetic TO Housing	Spectroscopy	
Monitor Diode		



Absolute Maximum Ratings

	Symbol	Unit	min	typ	max
Storage Temperature	T_S	°C	- 20		85
Operational Temperature at Case	T_{C}	°C	-20		50
Forward Current	I_{F}	mA			180
Reverse Voltage	V_R	V			0
Output Power	P_{opt}	mW			90

Stress in excess of the Absolute Maximum Ratings can cause permanent damage to the device.

Recommended Operational Conditions

	Symbol	Unit	min	typ	max
Operational Temperature at Case	T_{C}	°C	15		40
Forward Current	I _F	mA			170
Output Power	P_{opt}	mW			80

Measurement Conditions / Comments				

Characteristics at T_{LD} = 25 °C at Begin Of Life

Parameter	Symbol	Unit	min	typ	max
Center Wavelength	λ_{C}	nm	920	930	940
Spectral Width (FWHM)	$\Delta\lambda$	nm			1
Temperature Coefficient of Wavelength	dλ / dT	nm / K		0.3	
Output Power @ I _F : 170 mA	P _{opt}	mW	80		
Slope Efficiency	η_{d}	W/A	0.6	0.8	
Threshold Current	I_{th}	mA			70
Cavity Length	L	μm		750	
Divergence parallel	$\Theta_{[]}$	0		10	
Divergence perpendicular	Θ_{\perp}	0		30	
	- 11	o			

Measurement Conditions / Comments
see images on page 4
total output measured with integrating sphere
FWHM
FWHM





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Characteristics at T _{amb} 25 °C at Begin Of Life con	t'd
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Parameter	Symbol	Unit	min	typ	max
Polarization				TE	
Spatial Mode (transversal)		TEM ₀₀			
Spectral Mode (longitudinal)		Single/Multi Mode			

Measurement Conditions / Comments
E field parallel to Pin 2 - Pin 3 - plane
Fundamental Mode
depending on operating conditions

Monitor Diode

Parameter	Symbol	Unit	min	typ	max
Monitor Detector Responsivity	I _{mon} / P _{opt}	μΑ / mW	0.5		10
Reverse Voltage Monitor Diode	$U_{R\ MD}$	V	3		5

Measurement Conditions / Comments
$U_R = 5 \text{ V}$





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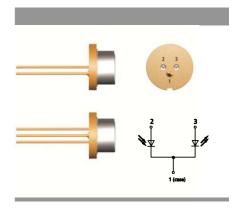
Package Dimensions

Parameter	Symbol	Unit	min	typ	max
Height of Emission Plane	d_{EP}	mm	2.30	2.45	2.50
Excentricity of Emission Center	R	mm			0.12
Pin Length	I _{PIN}	mm		14	

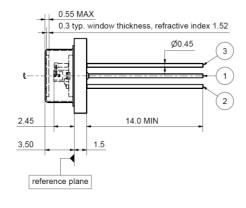
Measurement Conditions / Comments
reference plane: top side of TO header
reference: center of outer diameter of header

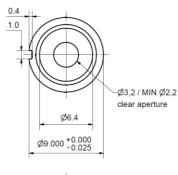
Package Pinout

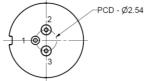
Ground	1
Photo Diode (+)	2
Laser (+)	3



Package Drawings







Z11-SPEC-SOT01-COM-0000





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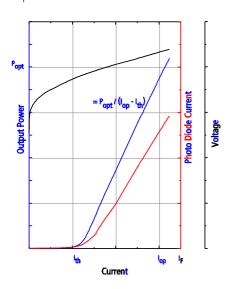
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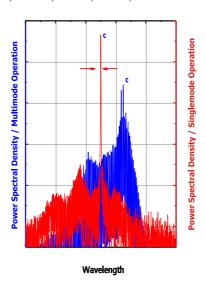


Typical Measurement Results

Output Power vs. Current



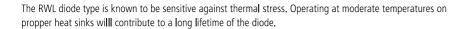
Spectra at Specified Optical Output Power



Performance figures, data and any illustrative material provided in this specification are typical and must be specifically confirmed in writing by eagleyard Photonics before they become applicable to any particular order or contract. In accordance with the eagleyard Photonics policy of continuous improvement specifications may change without notice.

Unpacking, Installation and Laser Safety

Unpacking the laser diodes should only be done at electrostatic safe workstations (EPA). Though protection against electro static discharge (ESD) is implemented in the laser package, charges may occur at surfaces. Please store this product in its original package at a dry, clean place until final use. During device installation, ESD protection has to be maintained.



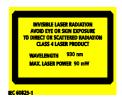
The laser emission from this diode is close to the invisible infrared region of the electromagnetic spectrum. Avoid direct and/or indirect exposure to the free running beam. Collimating the free running beam with optics as common in optical instruments will increase threat to the human eye.

Each laser diode will come with an individual test protocol verifying the parameters given in this document,













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